

**a 2000 0106**

The invention relates to the semiconducting photodetectors, particularly to detectors of ultraviolet radiation, and may be used in optoelectronic systems for determining the intensity and dose of ultraviolet radiation of the Sun and other light sources.

Summary of the invention consists in that the photodetector of ultraviolet radiation on base of structures with superficial potential barrier contains a layer of semiconductors  $A^{III}B^V$ , a tunnel-transparent layer of own oxide and a layer of  $SnO_2$  or ITO, in the semiconducting layer  $A^{III}B^V$  being formed a faulty layer, into which the life-time of the minor electric charge carriers is minimal. The faulty layer is placed at a distance from the semiconducting layer surface no more than the absorption depth of the visible radiation.